



IRF5305LPBF Information

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For Reference Only

Part Number IRF5305LPBF

Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET P-CH 55V 31A TO-262

Package TO-262-3 Long Leads, I2Pak, TO-262AA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IRF5305LPBF Specifications

Manufacturer Part Number IRF5305LPBF Manufacturer Infineon Technologies Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-262-3 Long Leads, 12Pak, TO-262AA Series HEXFET? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 55V Current - Continuous Drain (Id) @ 25°C 31A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 63nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1200pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 3.8W (Ta), 110W (Tc) Rds On (Max) @ Id, Vgs 60 mOhm @ 16A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-262 Package / Case TO-262-3 Long Leads, 12Pak, TO-262AA		
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SeriesHEXFET?FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)55VCurrent - Continuous Drain (Id) @ 25°C31A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs63nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1200pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)3.8W (Ta), 110W (Tc)Rds On (Max) @ Id, Vgs60 mOhm @ 16A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-262Package / CaseTO-262-3 Long Leads, 12Pak, TO-262AA		Transistors - FETs, MOSFETs - Single
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TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)55VCurrent - Continuous Drain (Id) @ 25°C31A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs63nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1200pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)3.8W (Ta), 110W (Tc)Rds On (Max) @ Id, Vgs60 mOhm @ 16A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-262Package / CaseTO-262-3 Long Leads, 12Pak, TO-262AA	Series	HEXFET?
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Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 63nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1200pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 60 mOhm @ 16A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-262-3 Long Leads, 12Pak, TO-262AA	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs63nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1200pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)3.8W (Ta), 110W (Tc)Rds On (Max) @ Id, Vgs60 mOhm @ 16A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-262Package / CaseTO-262-3 Long Leads, 12Pak, TO-262AA	Drain to Source Voltage (Vdss)	55V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) As W (Ta), 110W (Tc) Rds On (Max) @ Id, Vgs Operating Temperature Coperating Temperature Supplier Device Package Package / Case As W (Σ50μΑ 63nC @ 10V 1200pF @ 25V 1200V 1100m (Tc) 1100m (T	Current - Continuous Drain (Id) @ 25°C	31A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1200pF @ 25V Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 60 mOhm @ 16A, 10V Operating Temperature Operating Temperature Through Hole Supplier Device Package Package / Case 63nC @ 10V 1200pF @ 25V 25V 260 To-262-3 Long Leads, 12Pak, TO-262AA	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) E20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 60 mOhm @ 16A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-262 Package / Case TO-262-3 Long Leads, 12Pak, TO-262AA	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)3.8W (Ta), 110W (Tc)Rds On (Max) @ Id, Vgs60 mOhm @ 16A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-262Package / CaseTO-262-3 Long Leads, I2Pak, TO-262AA	Gate Charge (Qg) (Max) @ Vgs	63nC @ 10V
FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 60 mOhm @ 16A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Input Capacitance (Ciss) (Max) @ Vds	1200pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 60 mOhm @ 16A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-262 Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs60 mOhm @ 16A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-262Package / CaseTO-262-3 Long Leads, I2Pak, TO-262AA	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-262 Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Power Dissipation (Max)	3.8W (Ta), 110W (Tc)
Mounting Type Through Hole Supplier Device Package TO-262 Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Rds On (Max) @ Id, Vgs	60 mOhm @ 16A, 10V
Supplier Device Package TO-262 Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Mounting Type	Through Hole
	Supplier Device Package	TO-262
Report errors?	Package / Case	TO-262-3 Long Leads, I2Pak, TO-262AA
		Report errors?

IRF5305LPBF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRF5305LPBF Payment Methods





















IRF5305LPBF Shipping Methods













If you have any question about IRF5305LPBF, please do not hesitate to contact us!

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